Fabrice Iacovella, Ph.D.

Personal Details	**Born** in France, April 12th1988 **Nationality**: French **Marital status**: Single
Working address	Microelectronics Research Group (MRG) Institute of Electronic Structure and Laser (IESL) Foundation for Research and Technology (FORTH) 1st Floor, Physics Building, Univ. of Crete 70013, Vassilika Vouton, Herakleion, Crete, Greece Tel: +302810394112 Fax: +302810394105
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Education

March 2014	**Ph.D** in *Nano-physics, nano-devices, nano-measurements* Thesis on *"Electronic properties of quasi two-dimensional systems composed of few atomic layers under very intense magnetic field"* Laboratoire National des Champs Magnétiques Intenses, Toulouse, France
Dec 2011	**M.Sc** in *Fundamental Physics,* Thesis on *"Electronic properties of graphene under very intense magnetic field and low temperature"* Dpt. of Physics, University Toulouse III, France
July 2009	**B.Sc** in *Fundamental Physics,* *Dpt. of Physics, University Toulouse III, France*

Research Interests

- Graphene ballistic devices
- 2 dimensional transition metal dichalcogenide growth by Chemical Vapor Deposition (CVD) method
- 2 dimensional transition metal dichalcogenide electronics
- Novel devices for telecommunications and high speed (THz) electronics

Work experience

2017 – today

- **Postdoctoral fellow**
  - FORTH – IESL, Microelectronics Research Group, Herakleion, Greece
    - Growth of graphene by chemical vapor deposition on metallic thin films
    - Growth of molybdenum disulfide (MoS2) monolayer by chemical vapor deposition
    - Conception and characterization of MoS_2 FETs

2014 – 2016

- **Postdoctoral Fellow**
  - Crete Center for Quantum Complexity and Nanotechnology (CCQCN), University of Crete (Greece)
    - Growth of graphene by chemical vapor deposition on metallic thin films
    - Graphene and other 2D material electronics

- Design and characterization of Radio Frequency graphene devices
- Design and characterization of MoS_2 photodetectors

Experience& skills

- Experience in clean room activities (especially for optical and e-beam lithography, metal deposition, lift-off)
- Experience in micro-alignment of graphene flakes (transferring graphene upon boron nitride flakes)
- Experience with cryogenics (4He and 3He cryostats)
- Low-noise transport measurements under high (pulsed) magnetic field
- Experience in growth of graphene and MoS_2 by chemical vapor deposition method
- Electrical characterization of 2D materials transistors at Radio Frequencies
- Expertise in characterization of 2D materials by Raman spectroscopy

Languages *

**(Common European Framework of Reference for Languages)*

	Understanding		**Speaking**		**Writing**
	Listening	Reading	Spoken Interaction	Spoken production	
French	Native speaker				
English	Proficient (C2)	Proficient (C2)	Proficient (C2)	Proficient (C2)	Proficient (C2)
Greek	Independent user (B2)	Independent user (B2)	Independent user (B2)	Independent user (B2)	Independent user (B2)
Romanian	Independent user (B1)	Independent user (B1)	Independent user (B1)	Independent user (B1)	Independent user (B1)
Italian	Basic user (A2)	Basic user (A2)	Basic user (A2)	Basic user (A2)	Basic user (A2)
German	Basic user (A2)	Basic user (A2)	Basic user (A2)	Basic user (A2)	Basic user (A2)